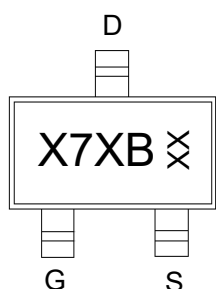


Features

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Application

- Battery protection
- Load switch
- Power management

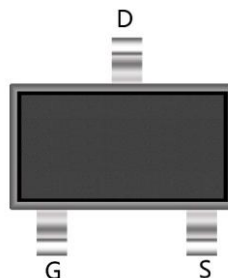


X7XB: Device code
XX: Code

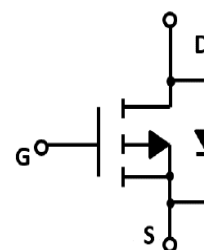
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-30V	40mΩ@-10V	-4.1A
	65mΩ@-4.5V	



SOT-23-3L top view



Schematic diagram

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V_{DS}	Drain-Source Breakdown Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}C$ -4.1	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}C$ -18	A
I_D	Continuous Drain Current	$T_C=25^{\circ}C$ -4.1	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}C$ 1.4	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	89	°C/W

Electrical Characteristics (T _J =25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	--	-2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-4.1A	--	40	52	mΩ
		V _{GS} =-4.5V, I _D =-3.7A	--	65	87	mΩ
Dynamic Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	310	--	pF
C _{OSS}	Output Capacitance		--	60	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	50	--	pF
Q _g	Total Gate Charge	V _{DS} =-15V, I _D =-4.1A, V _{GS} =-10V	--	14	--	nC
Q _{gs}	Gate Source Charge		--	1.6	--	nC
Q _{gd}	Gate Drain Charge		--	2.4	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =-15V, R _L =3.75Ω V _{GS} =-10V, R _G =3Ω	--	6	--	nS
t _r	Turn-on Rise Time		--	3.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	40	--	nS
t _f	Turn-Off Fall Time		--	10	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =-4.1A	--	--	-1.2	V

Typical Operating Characteristics

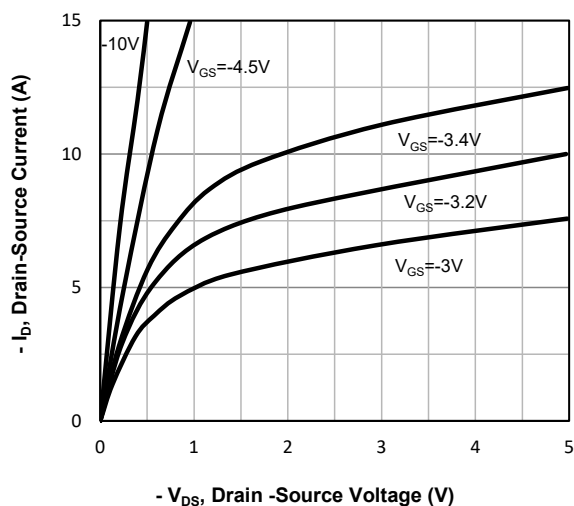


Fig1. Typical Output Characteristics

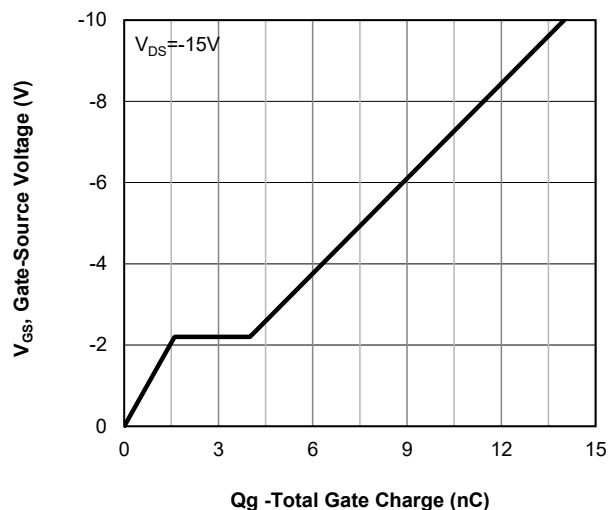


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

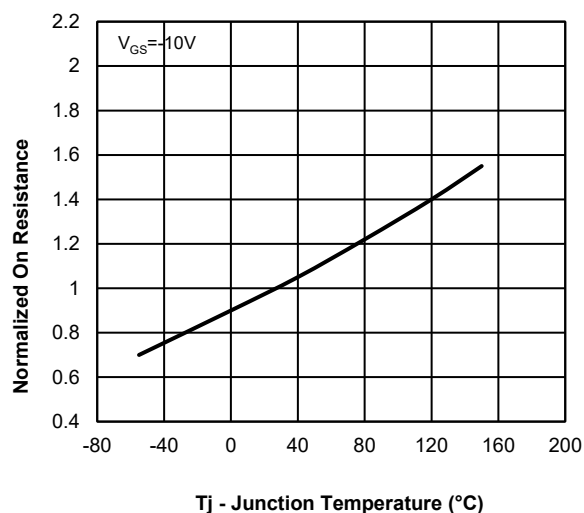


Fig3. Normalized On-Resistance Vs. Temperature

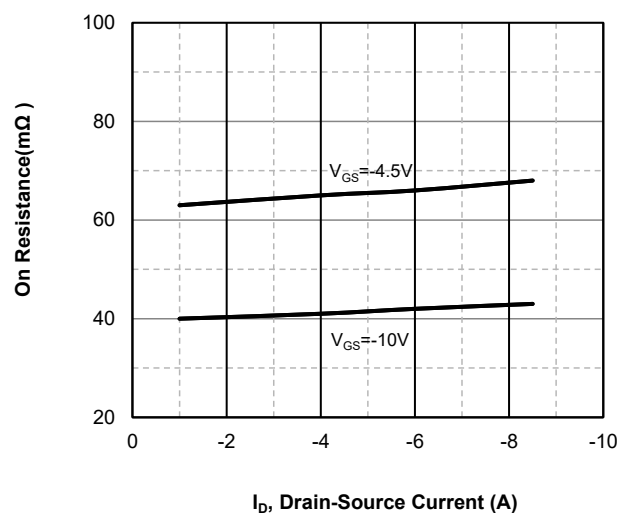


Fig4. On-Resistance Vs. Drain-Source Current

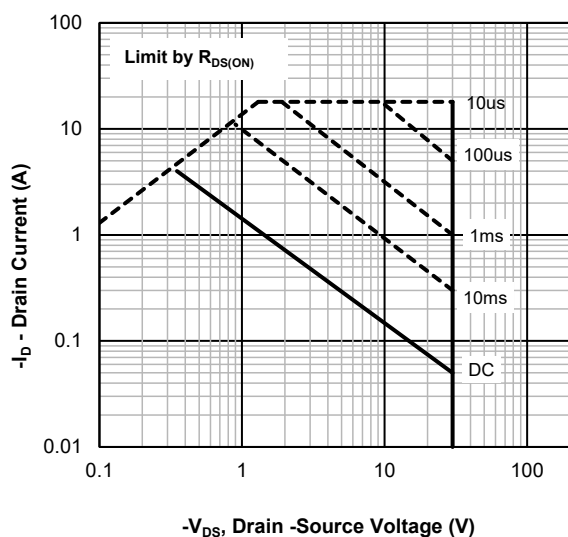


Fig5. Maximum Safe Operating Area

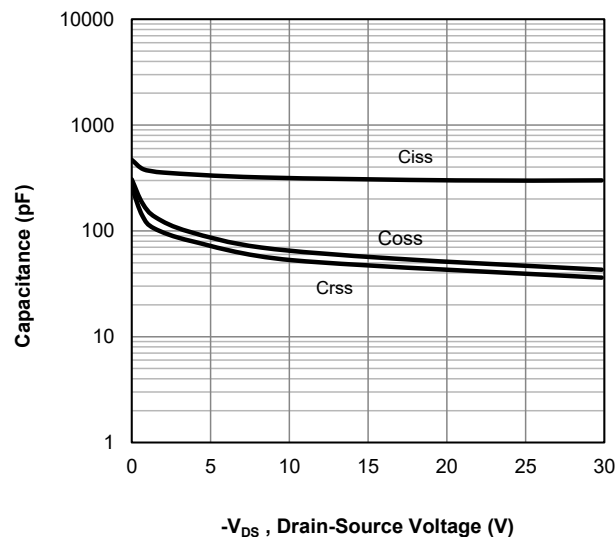
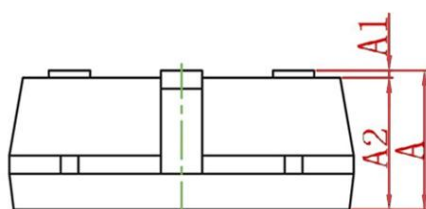
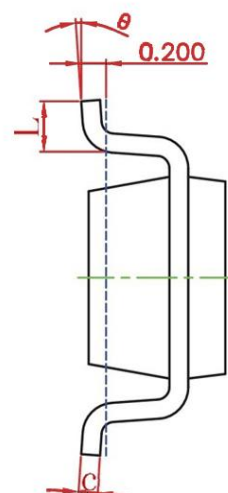
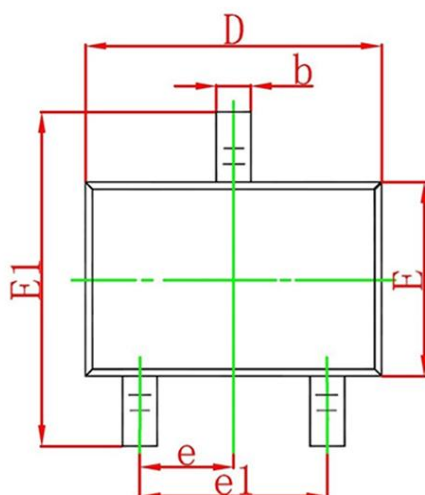


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-23-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.042	0.050
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.042	0.046
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.112	0.120
E	1.500	1.700	0.060	0.068
E1	2.650	2.950	0.106	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°